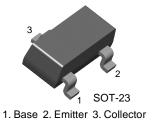


## **FJV1845**

### **Amplifier Transistor**

• Complement to FJV992



## **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

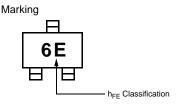
Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
I <sub>B</sub>	Base Current	10	mA
P <sub>C</sub>	Collector Dissipation	300	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =120V, I <sub>E</sub> =0			50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_C$ =0			50	nA
h <sub>FE1</sub>	DC Current Gain	$V_{CE}$ =6V, $I_{C}$ =0.1mA	150	580		
h <sub>FE2</sub>		$V_{CE}=6V, I_{C}=1mA$	200	600	1200	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =6V, $I_{C}$ =1mA	0.55	0.59	0.65	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.07	0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	50	110		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB}$ =30V, $I_{E}$ =0, f=1MHz		1.6	2.5	pF

## h<sub>FE2</sub> Classification

Classification	Р	F	E	U	
h <sub>FE2</sub>	200 ~ 400	300 ~ 600	400 ~ 800	600 ~ 1200	



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## **Typical Characteristics**

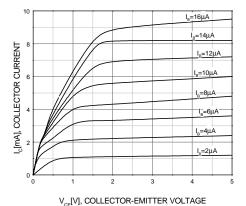


Figure 1. Static Characteristic

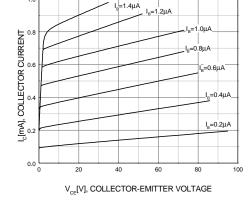


Figure 2. Static Characteristic

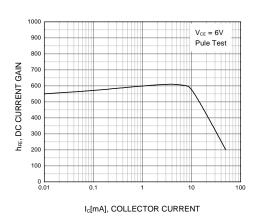


Figure 3. DC current Gain

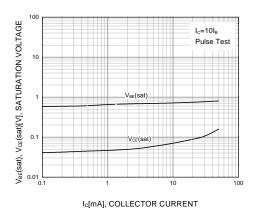


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

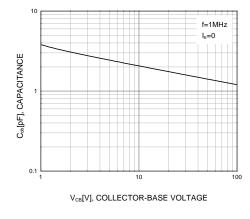


Figure 5. Collector Output Capacitance

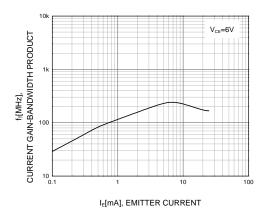
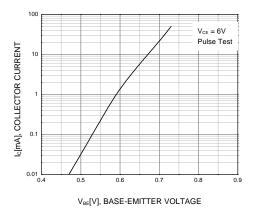


Figure 6. Current Gain Bandwidth Product

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# Typical Characteristics (Continued)



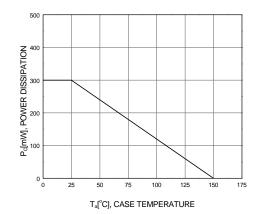


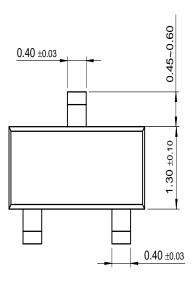
Figure 7. Collector Current vs. Base-Emitter Voltage

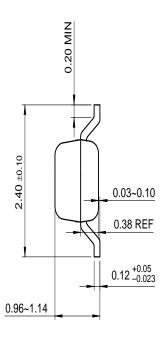
Figure 8. Power Derating

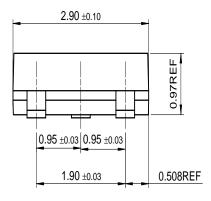
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# **Package Dimensions**

# **SOT-23**







Dimensions in Millimeters

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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C™	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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